N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	150V
● I_D	30A
● $R_{DS(ON)}$(at V_{GS}=10V)	24mΩ
● $R_{DS(ON)}$(at V_{GS}=6V)	26mΩ

● 100% EAS Tested

● 100% V_{DS} Tested

General Description

●Split gate trench MOSFET technology

0000S(on)

●Low $R_{DS(on)}$ & F 0 125204 842.04 r1 0 896.04 842.04 reW* n4BT/FBT/

Typical Electrical and Thermal Characteristics Diagrams

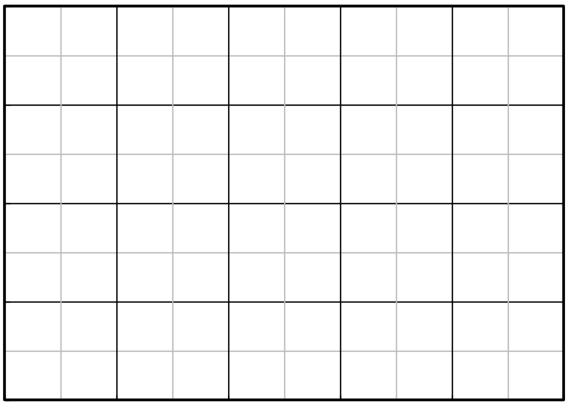


Figure 7. RDS(on) VS Drain Current

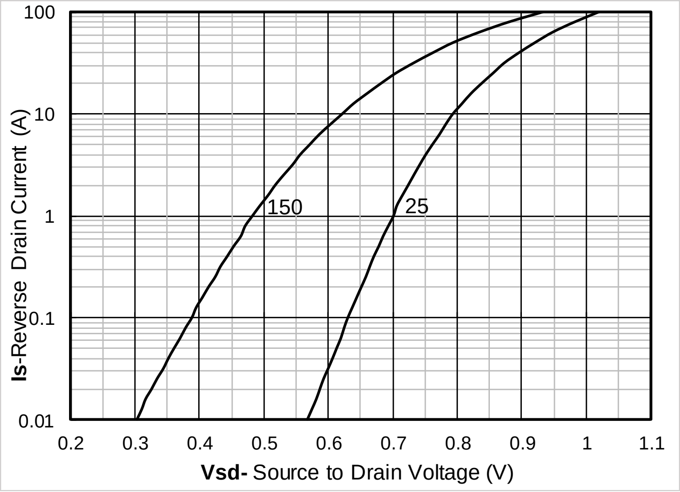


Figure 8. Forward characteristics of reverse diode

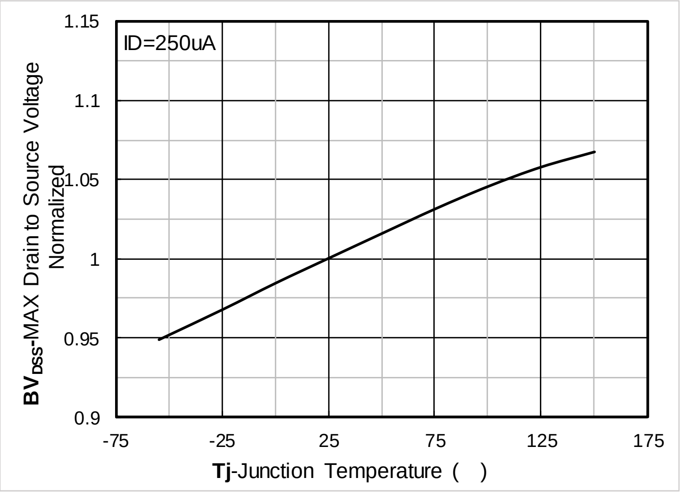


Figure 9. Normalized breakdown voltage

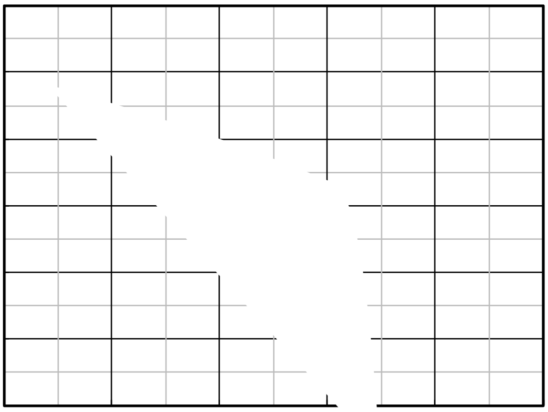


Figure 10. Normalized Threshold voltage

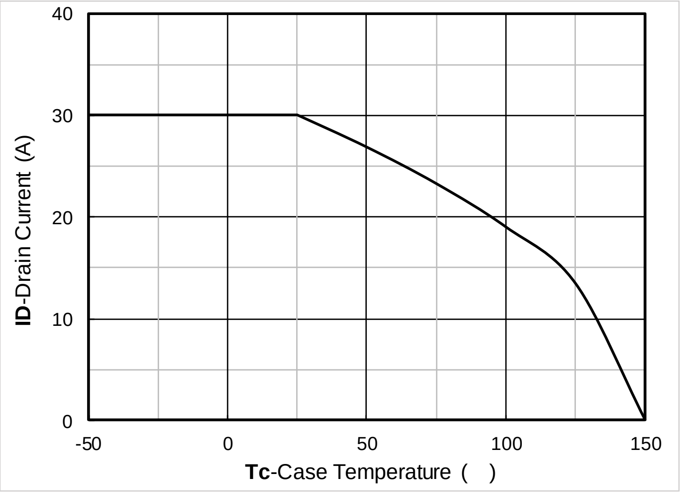


Figure 11. Current dissipation

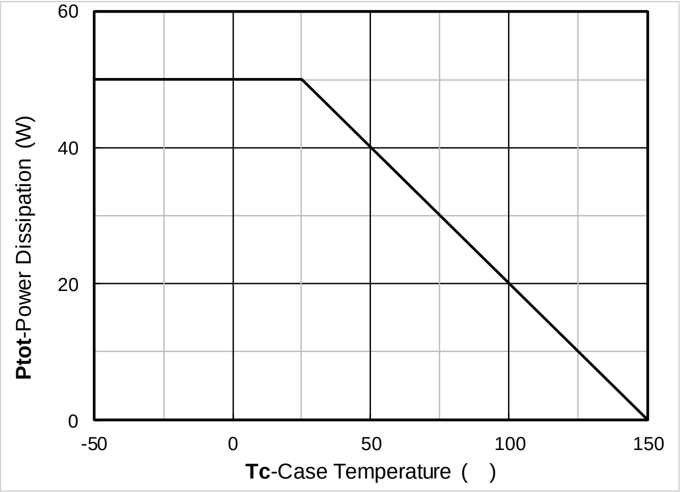


Figure 12. Power dissipation

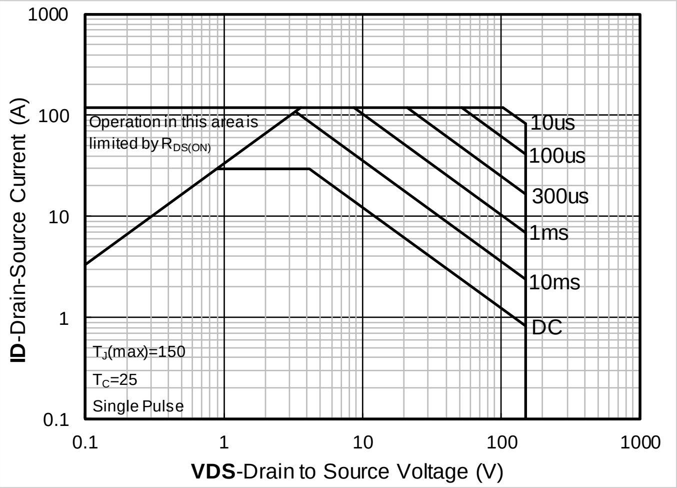


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

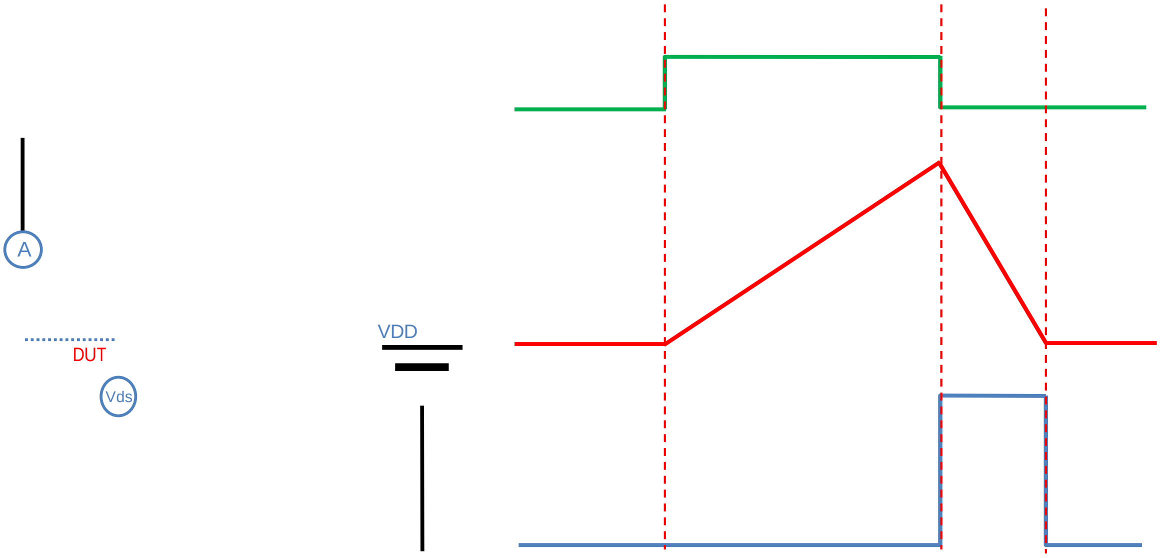
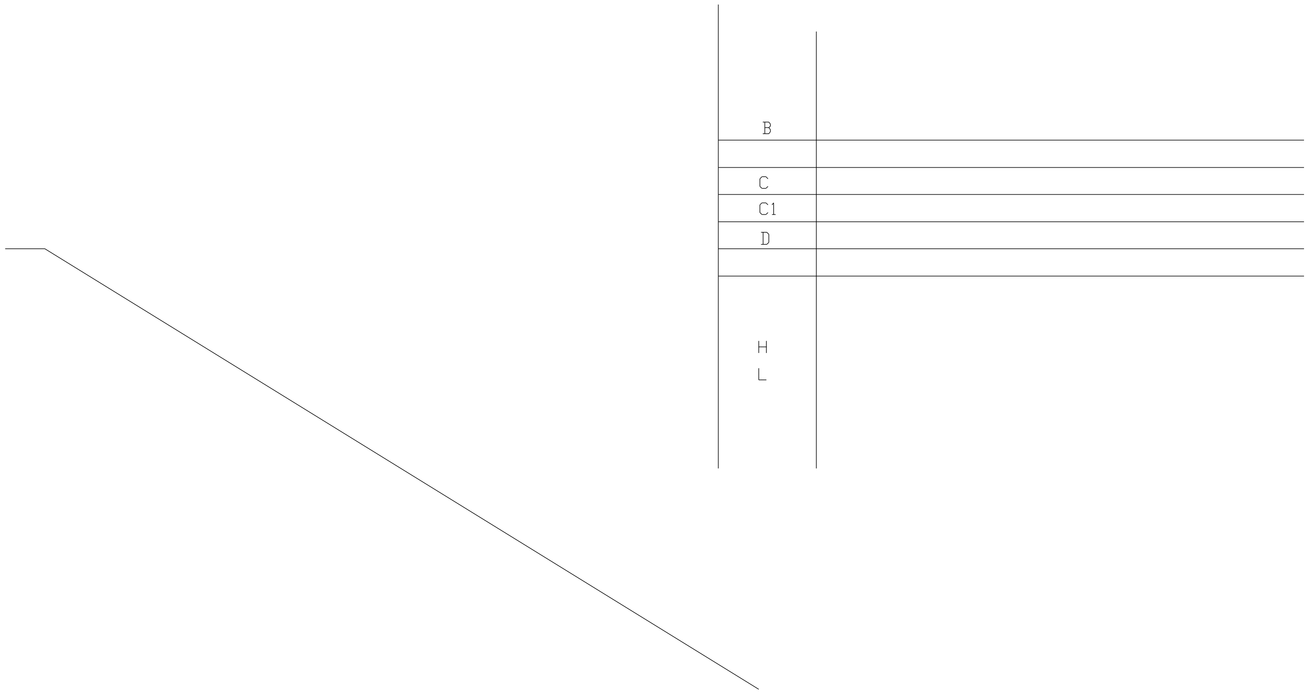


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

■ ITO-220AB-B Package information



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